



### **STP50NE08 Information**



For Reference Only

Part Number STP50NE08

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 80V 50A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

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# **STP50NE08 Specifications**

Manufacturer Part Number         STP50NE08           Manufacturer         STMicroelectronics           Category         Discrete Semiconductor Products           Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         80V           Current - Continuous Drain (Id) @ 25°C         50A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         5100pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         150W (Tc)           Rds On (Max) @ Id, Vgs         24 mOhm @ 25A, 10V           Operating Temperature         175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3		(III) 7() VII ()
Category  Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single  Package  TO-220-3  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  80V  Current - Continuous Drain (Id) @ 25°C  50A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  110nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  24 mOhm @ 25A, 10V  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  Package / Case		
Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         80V           Current - Continuous Drain (Id) @ 25°C         50A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         5100pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         150W (Tc)           Rds On (Max) @ Id, Vgs         24 mOhm @ 25A, 10V           Operating Temperature         175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3	Manufacturer	STMicroelectronics
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Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         80V           Current - Continuous Drain (Id) @ 25°C         50A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         5100pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         150W (Tc)           Rds On (Max) @ Id, Vgs         24 mOhm @ 25A, 10V           Operating Temperature         175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)80VCurrent - Continuous Drain (Id) @ 25°C50A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5100pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs24 mOhm @ 25A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)80VCurrent - Continuous Drain (Id) @ 25°C50A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5100pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs24 mOhm @ 25A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	-
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Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  10V  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  110nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  5100pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  24 mOhm @ 25A, 10V  Operating Temperature  175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-220AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  4V @ 250μA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  24 mOhm @ 25A, 10V  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-220-3	Drain to Source Voltage (Vdss)	80V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Through Hole  Supplier Device Package  Package / Case  110nC @ 10V  5100pF @ 25V  ±20V	Current - Continuous Drain (Id) @ 25°C	50A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  5100pF @ 25V  Vgs (Max)  ±20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  24 mOhm @ 25A, 10V  Operating Temperature  I75°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-220AB  TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB  Package / Case  TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs24 mOhm @ 25A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	110nC @ 10V
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Rds On (Max) @ Id, Vgs24 mOhm @ 25A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220AB  Package / Case TO-220-3	Power Dissipation (Max)	150W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	24 mOhm @ 25A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

### **STP50NE08** Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **STP50NE08 Payment Methods**



















### **STP50NE08 Shipping Methods**













If you have any question about STP50NE08, please do not hesitate to contact us!

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